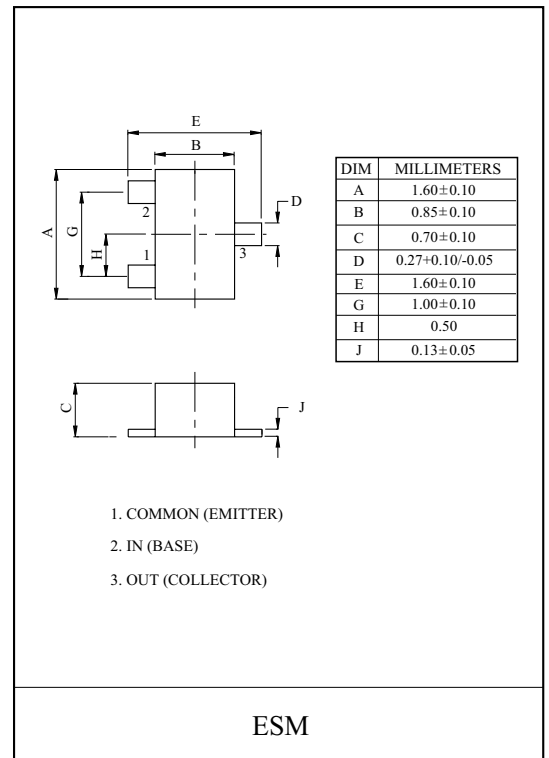
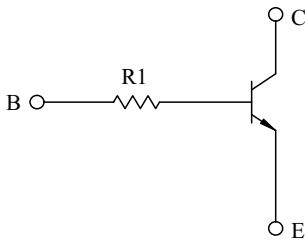


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.
- High Packing Density.

EQUIVALENT CIRCUIT



MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

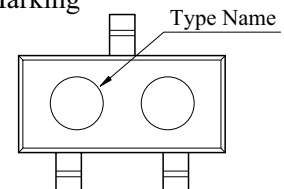
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	100	nA	
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	100	nA	
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=1mA$	120	-	-		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V	
Transition Frequency	f_T^*	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz	
Input Resistor	KRC410E	R_1		-	4.7	-	k Ω
	KRC411E			-	10	-	
	KRC412E			-	100	-	
	KRC413E			-	22	-	
	KRC414E			-	47	-	

MARK SPEC

TYPE	KRC410E	KRC411E	KRC412E	KRC413E	KRC414E
MARK	NK	NM	NN	NO	NP

Marking

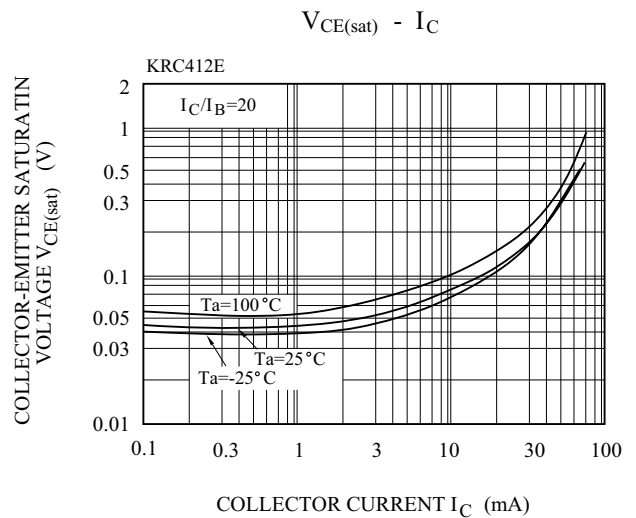
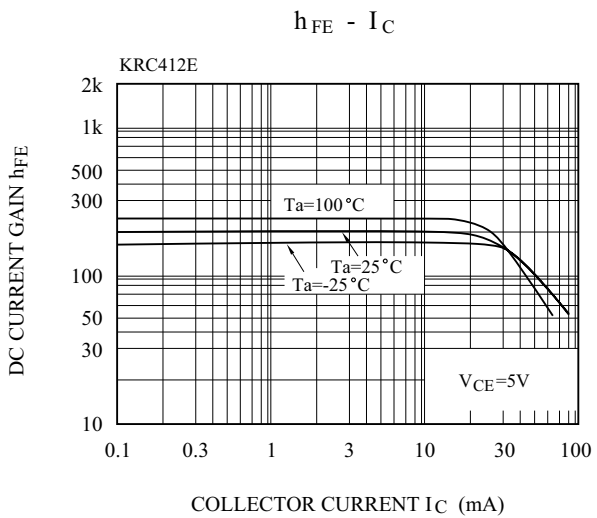
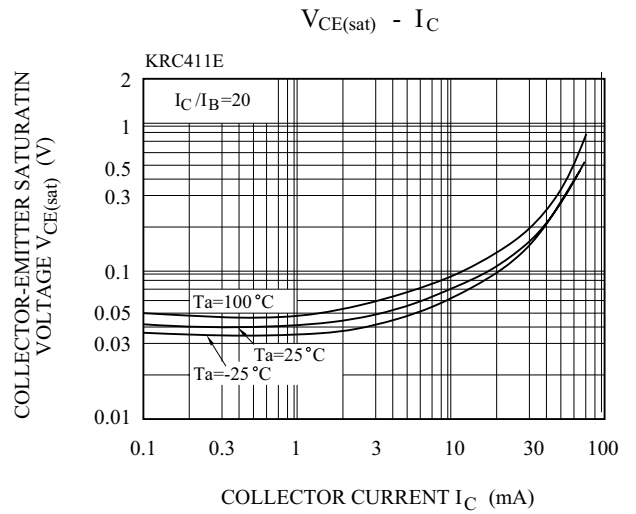
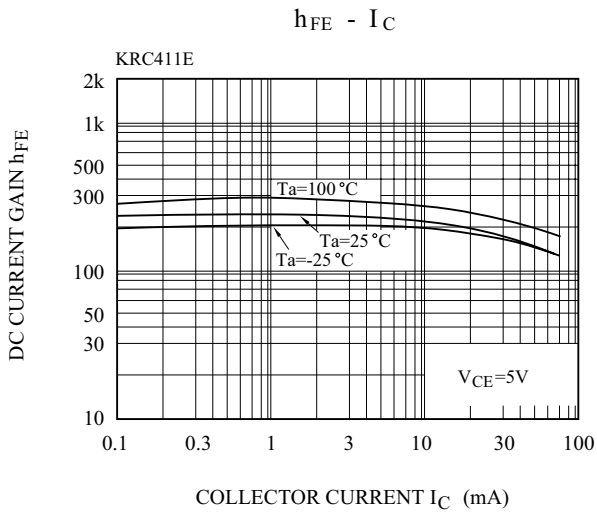
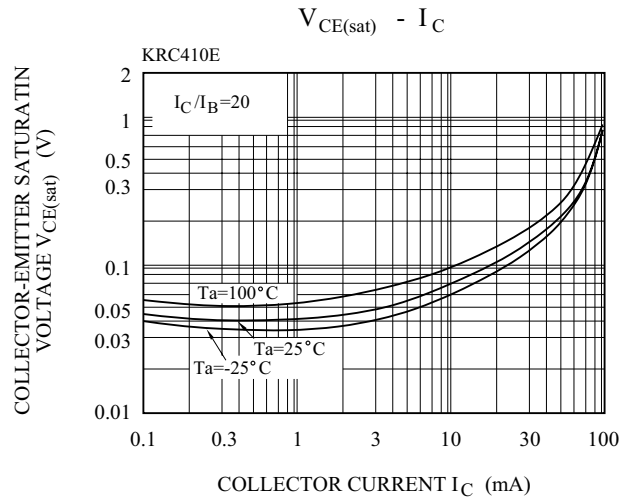
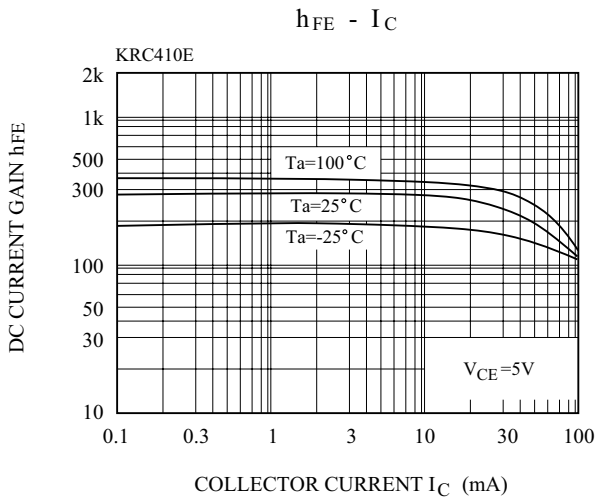


KRC410E~KRC414E

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Switching Time	Rise Time	KRC410E	V _O =5V V _{IN} =5V R _L =1k Ω	-	0.025	-	μS	
		KRC411E		-	0.03	-		
		KRC412E		-	0.3	-		
		KRC413E		-	0.06	-		
		KRC414E		-	0.11	-		
	Storage Time	KRC410E		t _{stg}	-	3.0		-
		KRC411E			-	2.0		-
		KRC412E			-	6.0		-
		KRC413E			-	4.0		-
		KRC414E			-	5.0		-
	Fall Time	KRC410E		t _f	-	0.2		-
		KRC411E			-	0.12		-
		KRC412E			-	2.0		-
		KRC413E			-	0.9		-
		KRC414E			-	1.4		-

KRC410E~KRC414E



KRC410E~KRC414E

